Screening of Excitons in Semiconductors, J. G. Gay [Phys. Rev. B **4**, 2567 (1971)]. There is an error in the above paper which causes the magnitude of the screening effects to be overestimated somewhat. The ideas and conclusions of the paper are not affected. The error can be corrected with the changes given below which consist of a list of corrected equations, and two corrected figures which account for the significant changes in the numerical results.

The error is introduced in Eq. (7) which should

$$W = \frac{1}{2\kappa_0} \int \frac{d^3q}{(2\pi)^3} \frac{1}{q^2} [\rho_e(\vec{q})\rho_h(-\vec{q}) + \rho_h(\vec{q})\rho_e(-\vec{q})] \left[1 + \left(\frac{1}{\kappa\vec{q}} - 1 \right) \right] + \frac{1}{2\kappa_0} \int \frac{d^3q}{(2\pi)^3} \frac{1}{q^2} [\rho_e(\vec{q})\rho_e(-\vec{q}) + \rho_h(\vec{q})\rho_h(-\vec{q})] \left(\frac{1}{\kappa(\vec{q})} - 1 \right), \quad (8)$$

$$W(r) = -\frac{e^2}{2\kappa_0} \int \frac{d^3q}{(2\pi)^3} \frac{1}{q^2} \left[(e^{-i\vec{q}\cdot\vec{r}} + e^{i\vec{q}\cdot\vec{r}}) \frac{1}{\kappa(\vec{q})} - 2 \left(\frac{1}{\kappa(\vec{q})} - 1 \right) \right], \quad (11)$$

$$W_{av} = \langle \psi(\vec{r}) | -\frac{e^2}{\kappa_0 r} | \psi(\vec{r}) \rangle + \frac{1}{4\pi^2\kappa_0} \int \frac{d^3q}{q^2} \rho(\vec{q})\rho(-\vec{q}) \left(\frac{1}{\kappa(\vec{q})} - 1 \right), \quad (19)$$

$$V_{av}(r) = -\frac{e^2}{\kappa_0 r} + \frac{1}{4\pi^2\kappa_0} \int \frac{d^3q}{q^2} \left(\frac{1}{\kappa(\vec{q})} - 1 \right) \left\{ e \int d^3x e^{-i\vec{q}\cdot\vec{x}} \left[\left(\frac{M}{m_e} \right)^3 \delta \left(\frac{M\vec{x}}{m_e} - \vec{r} \right) - \left(\frac{M}{m_h} \right)^3 \delta \left(\frac{M\vec{x}}{m_h} - \vec{r} \right) \right] \rho(-\vec{q}) - 2e^2 \right\}, \quad (23)$$

$$V(r) = -(e^2/\kappa_0) e^{-Qr}/r, \quad (27)$$

$$W_\infty = -e^2 Q/\kappa_0, \quad (28)$$

$$W_\infty = -\frac{2e^2}{\kappa_0 \pi} Q \tan^{-1} \frac{q_{\max}}{Q}. \quad (38)$$

Because (19), (27), and (28) are changed, Fig. 1 should be replaced by the Fig. 1 shown here.

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$$W = \frac{1}{2} \int \frac{d^3q}{(2\pi)^3} \rho(\vec{q}) [\phi(-\vec{q}) + \delta\phi(-\vec{q})] = \frac{1}{2\kappa_0} \int \frac{d^3q}{(2\pi)^3} \frac{4\pi}{q^2} \rho(\vec{q}) [\rho(-\vec{q}) + \delta\rho(-\vec{q})], \quad (7)$$

because the energy density in a dielectric medium is $(1/8\pi) \vec{E} \cdot \vec{D}$ instead of $(1/8\pi) E^2$ as is implied by the original Eq. (7). The other equations which are affected by the error appear corrected in the following list:

The curves of Fig. 2, which give the effect of screening on the continuum enhancement, are also incorrect since they were calculated using the potential of the original Eq. (27). Because the correct Debye-Hückel potential corresponds to weaker screening than the incorrect potential, the effect of repeating the calculation using the Debye-Hückel

FIG. 1. Corrected version of Fig. 1. The original caption is not changed.

FIG. 3. Corrected version of Fig. 3. The original caption is not changed.

potential would be to increase the carrier concentration at which a given decrease in the enhancement occurs. Since this would actually reinforce the conclusions drawn from the original calculation, the calculation has not been redone.

Finally, because of the corrections in Fig. 1 and the correction to Eq. (38), Fig. 3 should be replaced by the Fig. 3 shown here.

I wish to emphasize that the ideas and conclusions of the original paper are not affected by the corrections described here, since they are not sensitive to the precise magnitude of the screening energy shifts.

I am most grateful to Dr. W. D. Johnston for bringing the error to my attention.

Migration Energy of an Interstitial He Atom in LiH, S. S. Jaswal and M. E. Striefler [Phys. Rev. B 1, 4118 (1970)]. Due to a programming error the results for the formation energy of an interstitial He atom in the face-centered position in LiH are wrong. For $\alpha(\text{H}^+) = 1$, the formation energy for the face-centered position is 2.33 eV instead of 2.727 eV. This changes the interstitial migration energy from 0.65 to 0.253 eV.

Effect of Hydrostatic Pressure and Pd Doping on the Fermi Surface of AuGa₂, J. E. Schirber [Phys. Rev. B 6, 333 (1972)]. The values of x in Au_{1-x}Pd_xGa₂ quoted throughout the paper should be multiplied by 1.85.